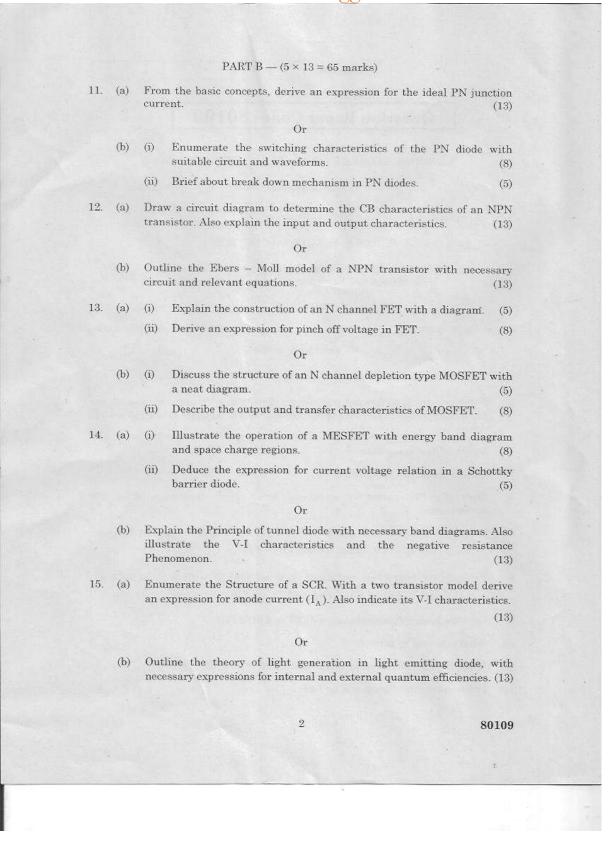
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B.E./B.Tecl	a. DEGREE EXAMINATIONS, APRIL/MAY 2019.
	Second Semester
	Medical Electronics
	EC 8252 — ELECTRONIC DEVICES
	to Electronics and Communication Engineering/ ronics and Telecommunication Engineering)
	(Regulation 2017)
Time: Three hours	Maximum : 100 marks
	Answer ALL questions.
	PART A — $(10 \times 2 = 20 \text{ marks})$
	tal forward bias current density in a PN junction diode under rd bias voltage of 0.65 V at 300 K. Assume $J_S=4.155\times 10^{-11}$
2. Define Diffusion	capacitance.
3. What is meant by	"Early effect"?
4. State the "h" configuration.	parameter equations for a NPN transistor under CE
	internal pinch off voltage of JFET with $\alpha=0.75\mu m$, = 11.6 and $\varepsilon_0=8.854\times 10^{-12}F/m$.
	by effect coefficient (y) in a MOSFET with $N_a=3\times10^{16}/{\rm cm}^3$, $=8.854\times10^{-12}{\rm F/m}\ {\rm and}\ C_{\rm ox}=1.726\times10^{-7}{\rm F/cm}^2.$
7. Give the basic did	ference between JFET and MESFET.
8. What is meant by	tunneling?
9. What do you und	erstand by intrinsic standoff ratio in an UJT?
10. Define quantum	efficiency in an LED.

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